

ESE370: Circuit-Level Modeling, Design, and Optimization for Digital Systems

Lec 3: September 10, 2021
Transistor Introduction (first order)

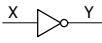


Today

- Basic Digital Gates
- Boolean Logic
 - Basic Algebra
 - DeMorgan's Law
 - Minimum Sum of Products/K-maps
- Cascading Gates
- Transistor first order model
 - For performance estimates (i.e propagation delay!)
 - There are always Rs and Cs!

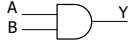
Basic Digital Gates

NOT
 $Y = \bar{X}$



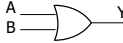
X	Y
0	1
1	0

AND
 $Y = A \cdot B$



A	B	Y
0	0	0
0	1	0
1	0	0
1	1	1

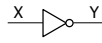
OR
 $Y = A + B$



A	B	Y
0	0	0
0	1	1
1	0	1
1	1	1

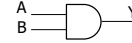
Basic Digital Gates

NOT
 $Y = \bar{X}$




X	Y
0	1
1	0

AND
 $Y = A \cdot B$

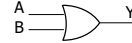


A	B	Y	Z
0	0	0	1
0	1	0	1
1	0	0	1
1	1	1	0

NAND
 $Z = \overline{A \cdot B}$




OR
 $Y = A + B$



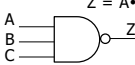
A	B	Y	Z
0	0	0	1
0	1	1	0
1	0	1	0
1	1	1	0

NOR
 $Z = \overline{A + B}$



Basic Digital Gates

NAND
 $Z = \overline{A \cdot B \cdot C}$



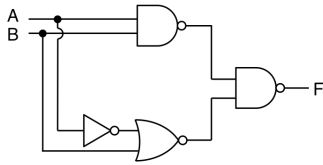
A	B	C	Z
0	0	0	1
0	0	1	1
0	1	0	1
0	1	1	1
1	0	0	1
1	0	1	1
1	1	0	1
1	1	1	0

Boolean Algebra

□ TABLE 2-3
Basic Identities of Boolean Algebra

1. $X + 0 = X$	2. $X \cdot 1 = X$	
3. $X + 1 = 1$	4. $X \cdot 0 = 0$	
5. $X + X = X$	6. $X \cdot X = X$	
7. $X + \bar{X} = 1$	8. $X \cdot \bar{X} = 0$	
9. $\bar{\bar{X}} = X$		
10. $X + Y = Y + X$	11. $XY = YX$	Commutative
12. $X + (Y + Z) = (X + Y) + Z$	13. $X(YZ) = (XY)Z$	Associative
14. $X(Y + Z) = XY + XZ$	15. $X + YZ = (X + Y)(X + Z)$	Distributive
16. $\overline{X + Y} = \bar{X} \cdot \bar{Y}$	17. $\overline{X \cdot Y} = \bar{X} + \bar{Y}$	DeMorgan's

Combination



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7

7

Boolean Expressions

- Sum-of-products form (SOP)
 - Eg. $ABC+DEF+GHI$
- Product-of-sums form (POS)
 - Eg. $(A+B+C)(D+E+F)(G+H+I)$
- Convert between the two with Boolean algebra

- DeMorgan's Law

$$A + B = \overline{\overline{A} \cdot \overline{B}}$$

$$A \cdot B = \overline{\overline{A} + \overline{B}}$$

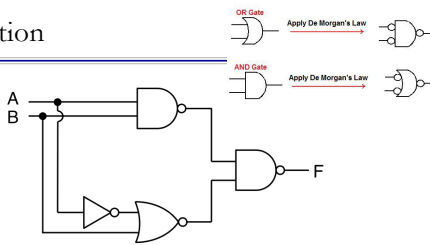


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8

Combination



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9

Canonical Form

- Every minterm in your expression has every variable

Row Number	A	B	C	f
0	0	0	0	0
1	0	0	1	0
2	0	1	0	0
3	0	1	1	1
4	1	0	0	0
5	1	0	1	0
6	1	1	0	1
7	1	1	1	1

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10

10

Canonical Form

- Every minterm in your expression has every variable

Row Number	A	B	C	f
0	0	0	0	0
1	0	0	1	0
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3	0	1	1	1
4	1	0	0	0
5	1	0	1	0
6	1	1	0	1
7	1	1	1	1

$$f(A, B, C) = ABC + \overline{A}BC + A\overline{B}C$$

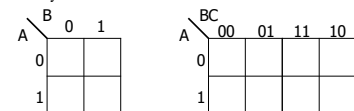
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11

11

What is a K(arnaugh)-map?

- A grid of squares (representing truth table)
- Each square represents one minterm
- The minterms are ordered according to Gray code
 - Only one variable changes between adjacent squares
- Squares on edges are considered adjacent to squares on opposite edges
 - I.e. Table wraps around
- K-maps are clumsy with more than 4 variables



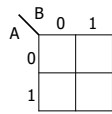
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12

12

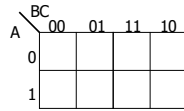
K-map Examples (Preclass 1)

- 2-variable



Eg: $Z = A'B' + AB' + A'B$

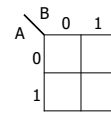
- 3-variable



13

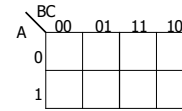
K-map Examples (Preclass 2)

- 2-variable



Eg: $Z = A'B' + AB' + A'B$

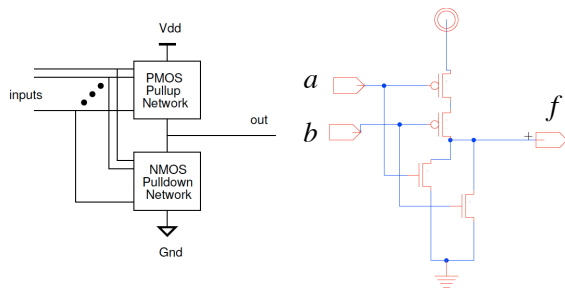
- 3-variable



Eg: $Z = A'B'C' + A'B + ABC' + AC$

14

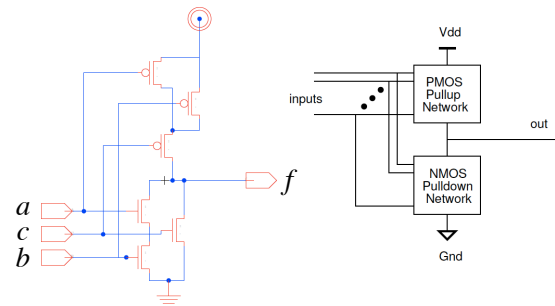
Static CMOS Gate Structure



15

Gate Design Example

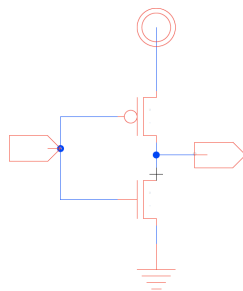
- Design gate to perform: $f = (\bar{a} + \bar{b}) \cdot \bar{c}$



16

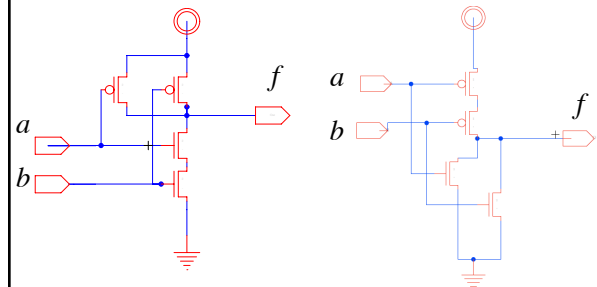
Inverting Stage

- Each stage of Static CMOS gate is inherently inverting



17

NAND/NOR Fundamental Gates



18

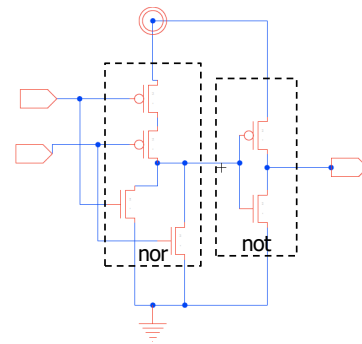
How implement OR?

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19

19

How implement OR?



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20

20

Cascading Stages

- Can always cascade “stages” to build more complex gates
- Could simply build nor2 or nand2 at circuit level and assemble arbitrary logic by combining – universality
 - but may not be smallest/fastest/least power

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21

21

Implement: $f = a \cdot \bar{b}$

- Pullup?
- Pulldown?

Hint: use cascading stages

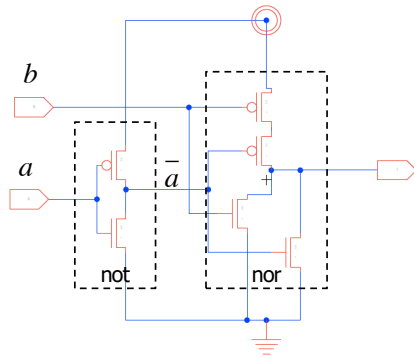
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22

Implement: $f = a \cdot \bar{b}$

- Pullup?
- Pulldown?



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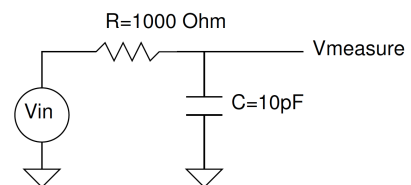
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23

Final Voltage? (Preclass 4)

Assume V_{in} is 0 for $t < 0$ and steps to 1V at $t = 0$.

What value does $V_{measure}$ take on as $t \rightarrow \infty$?



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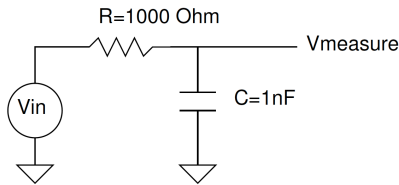
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Final Voltage?

Assume V_{in} is 0 for $t < 0$ and steps to 1V at $t = 0$.

What value does $V_{measure}$ take on as $t \rightarrow \infty$?



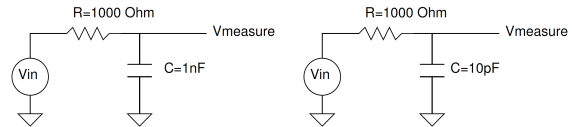
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25

Final Voltage?

□ Bonus question: Which one will settle faster?



A

B

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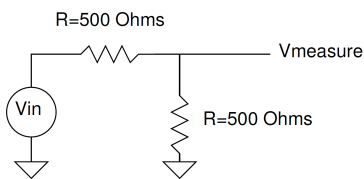
26

26

Final Voltage?

Assume V_{in} is 0 for $t < 0$ and steps to 1V at $t = 0$.

What value does $V_{measure}$ take on as $t \rightarrow \infty$?



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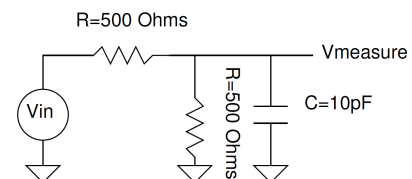
27

27

Final Voltage?

Assume V_{in} is 0 for $t < 0$ and steps to 1V at $t = 0$.

What value does $V_{measure}$ take on as $t \rightarrow \infty$?



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28

28

Conclude?

□ DC/Steady-State

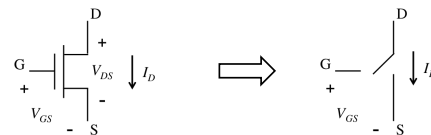
- Ignore the capacitors
- Look like “open circuit”

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29

29

MOSFET – Zeroeth Order Model



□ Ideal Switch

$V_{GS} > V_{th} \rightarrow$ switch is closed, conducts

$V_{GS} < V_{th} \rightarrow$ switch is open, does not conduct

□ Gate draws no current from input

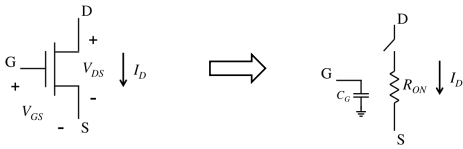
- Loads input capacitively (gate capacitance)

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30

30

First Order Model

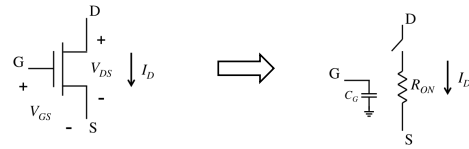


□ Switch

- Loads gate input capacitively
 - C_g
- Has finite drive strength
 - R_{on}

31

First Order Model



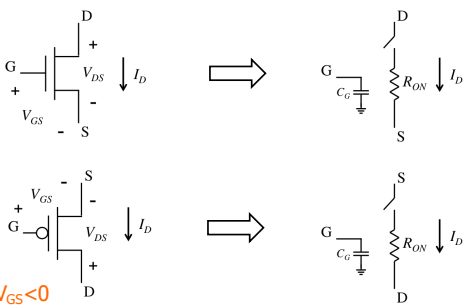
□ Switch

- Loads gate input capacitively
 - C_g
- Has finite drive strength
 - R_{on}

What do drive and load mean?

32

First Order Model - PMOS

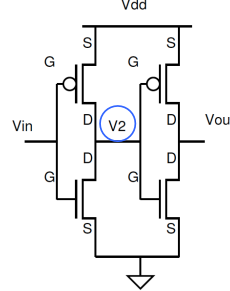


$V_{DS}, V_{GS} < 0$

33

CMOS Buffer Gate

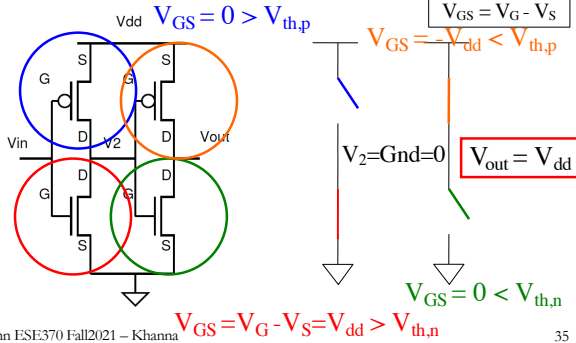
Stage 1 Stage 2



34

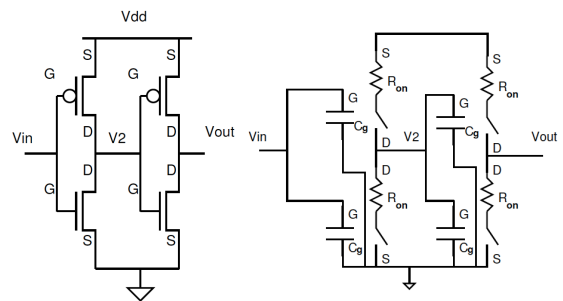
Reminder: Zero-Order Model?

What happens when $V_{in} = V_{dd} > V_{th,n}$?



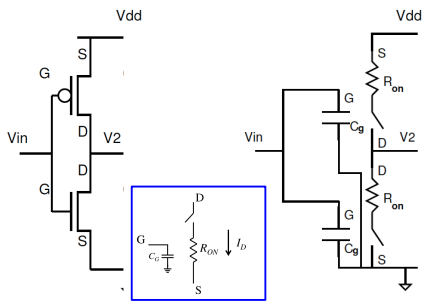
35

CMOS Buffer Gate - First Order



36

CMOS Buffer Gate - First Order

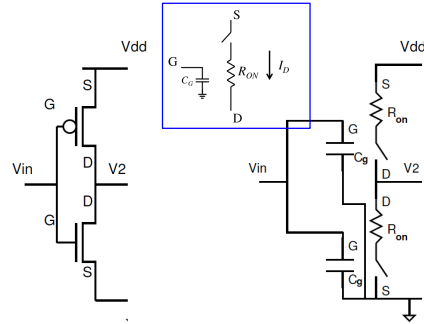


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37

37

CMOS Buffer Gate - First Order

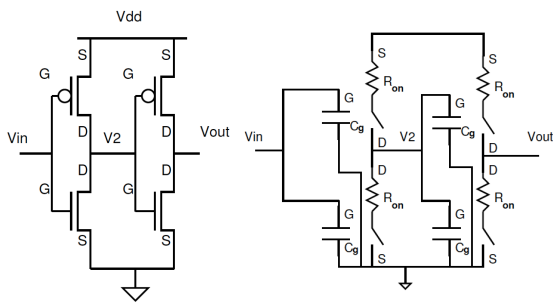


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38

38

CMOS Buffer Gate - First Order

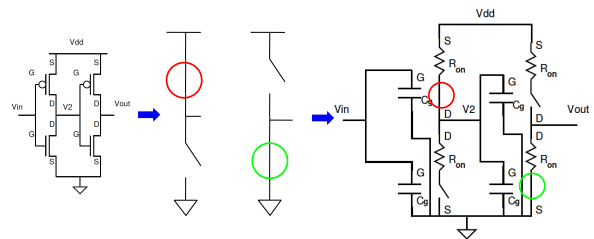


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39

39

Zero-Order Model to Set Switches



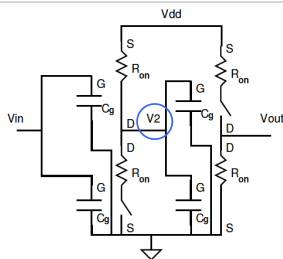
What is V_{IN} for this switch pattern?

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40

40

CMOS Buffer Gate - First Order



ESE215 problem

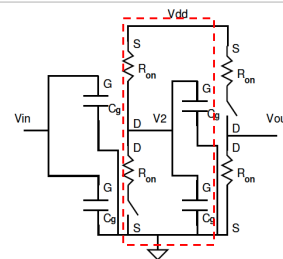
Leaves an RC Circuit we can analyze

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41

41

CMOS Buffer Gate - First Order



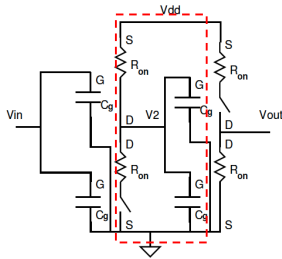
Look at intermediary node V_2
 Connected to output of stage 1 and input of stage 2

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42

42

CMOS Buffer Gate - First Order



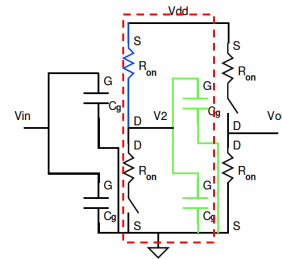
- What is equivalent circuit for the gate output of stage 1 driving V_2 ? What is load on the output of stage 1?

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43

43

CMOS Buffer Gate - First Order



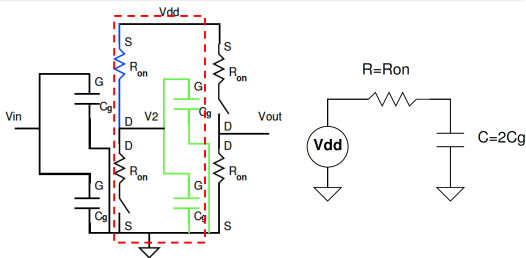
- Stage 1 equivalent circuit for the gate output
- Load on V_2
 - Capacitive, input of stage 2

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44

44

CMOS Buffer Gate - First Order



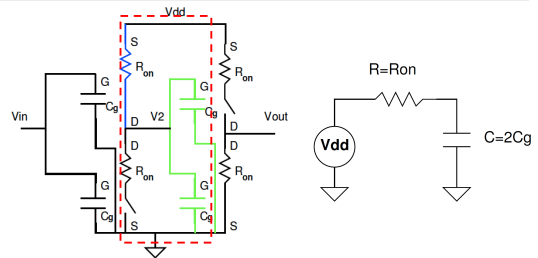
- Stage 1 equivalent circuit for the gate output
- Load on V_2
 - Capacitive, input of stage 2

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45

45

CMOS Buffer Gate - First Order



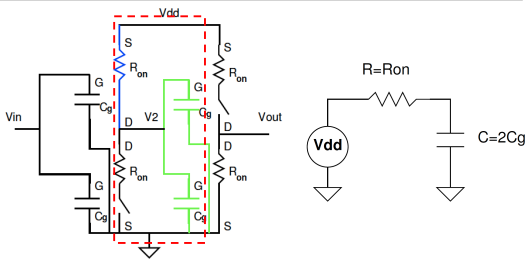
- What is time constant of V_2 when V_{in} switches from V_{DD} to 0?

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46

46

CMOS Buffer Gate - First Order



- What is time constant of V_2 when V_{in} switches from V_{DD} to 0?
 - $\tau = 2R_{on}C_g$

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47

47

First-Order Model

- Includes settling times/delay
- Voltage settling with capacitive loads
 - At least some basis for reasoning about delay

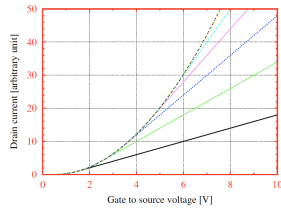
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48

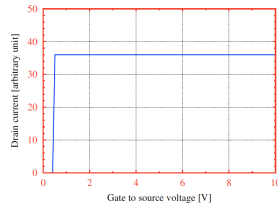
48

What is still missing?

IV curve



1st Order



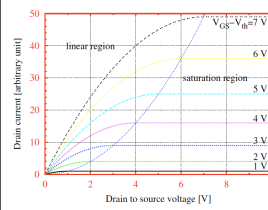
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49

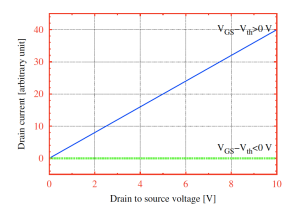
49

What is still missing?

IV curve



1st Order



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50

50

What is still missing?

- What happens at intermediate voltages?
 - When the input is not rail-to-rail (not just gnd or V_{dd} inputs)
- Details of dynamics, including...
 - Input transition is not an ideal step
 - Intermediate drive strengths change with V_{GS}
 - Drain resistance changes
- Sub-threshold operation
 - When $V_{GS} < V_{th}$

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51

51

Design: Engineering Control

- V_{th}
 - Process engineer
- Drive strength (R_{on})
 - Circuit engineer
 - Control with sizing transistors
- Supply voltages (V_{dd})
 - Range set by process engineer
 - Detail use by circuit engineer

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52

52

Big Ideas

- MOSFET Transistor as switch
 - With limited drive
- Purpose-driven simplified modeling
 - Aid reasoning, sanity check, simplify design
- Analysis methodology
 - Zero order to understand switch state (logic)
 - First-order to get equivalent RC circuit (delay)

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53

53

Admin

- Diagnostic grades recorded
 - Solutions posted online (pdf in Canvas)
 - Make sure you understand
 - Diagnose what you need to review and study
 - Karnaugh maps (minimum sum of products), RC capacitive settling (time constant), and wire resistive and capacitive properties
- HW 1 due **Tuesday** 9/14 next week
 - Because you need Monday lecture for noise margins
 - Can look at last year's lecture slides if you want to look ahead
 - HW due following **Monday** 9/20

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54

54